

Silicon NPN Power Transistors

2SC1722

DESCRIPTION

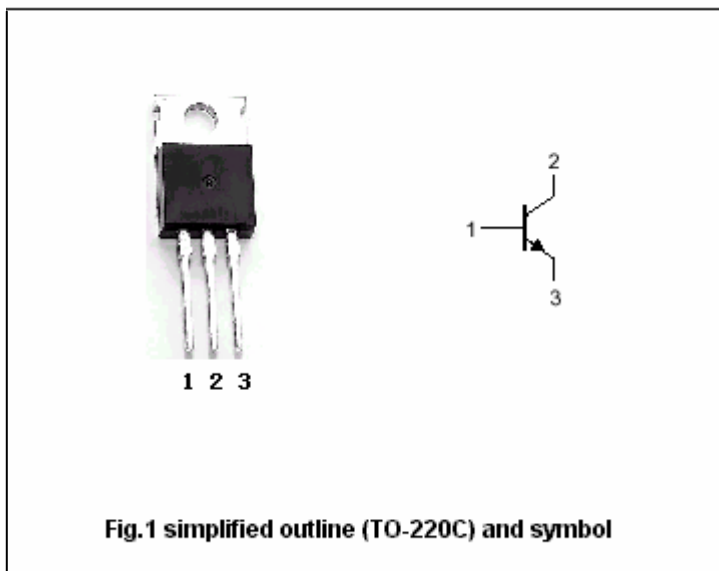
- With TO-220C package
- High breakdown voltage
- High transition frequency

APPLICATIONS

- Low frequency power amplifier
- TV horizontal/vertical driver

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	300	V
V _{CEO}	Collector-emitter voltage	Open base	300	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		0.2	A
P _C	Collector power dissipation	T _a =25°C	1.8	W
		T _C =25°C	12.5	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-45~150	°C

Silicon NPN Power Transistors

2SC1722

CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =5mA ; R _{BE} =∞	300			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =100μA ; I _E =0	300			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =100μA ; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =50mA; I _B =5mA		1.0	2.0	V
V _{BE}	Base-emitter on voltage	I _C =50m A ; V _{CE} =10V		0.68	0.9	V
I _{CBO}	Collector cut-off current	V _{CB} =250V ; I _E =0			0.1	μA
I _{CEO}	Collector cut-off current	V _{CE} =250V; R _{BE} =∞			2	μA
h _{FE}	DC current gain	I _C =50m A ; V _{CE} =10V	50		300	
f _T	Transition frequency	I _C =30m A ; V _{CE} =20V		80		MHz
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =50V; f=1MHz		4.3		pF

Silicon NPN Power Transistors

2SC1722

PACKAGE OUTLINE



Fig.2 Outline dimensions (unindicated tolerance: ±0.10 mm)